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## Spin and charge transport in graphene devices in the classical and quantum regimes

Diniz Guimaraes, Marcos Henrique

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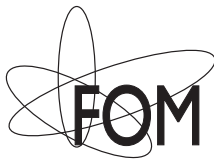
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Spin and Charge Transport in Graphene Devices  
in the Classical and Quantum Regimes

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**SPIN AND CHARGE TRANSPORT IN GRAPHENE DEVICES  
 IN THE CLASSICAL AND QUANTUM REGIMES**

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to obtain the degree of PhD at the  
 University of Groningen  
 on the authority of the  
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*sub specie æternitatis*



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